

# SEMICONDUCTOR NETWORKS

ZETEX SEMICONDUCTORS

Zetex Semiconductor networks are arrays of interconnected or isolated semiconductor dice encapsulated in a single multilead package.

In addition to a useful range of standard arrays, we also offer a **custom-build engineering service** to design network package layouts to meet customers' own specifications. Networks can be designed to replace directly discrete semiconductor assemblies.

## STANDARD PRODUCTS — SILICON PLANAR QUAD TRANSISTORS

This range of products covers Bipolar and Mosfet Quads in a single moulded or ceramic dual in-line package. Their applications range from small signal amplification through to medium power switching and core driving.

- FF3725JA Approved to BS/CECC 50004 019

## MOSFET QUADS (Plastic D.I.L.)

at 25°C ambient temperature (each transistor)

Type	BV <sub>DSS</sub>	I <sub>D</sub> mA	I <sub>DM</sub> A	V <sub>GS(th)</sub>			Ω at Max.	R <sub>DS(on)</sub> I <sub>D</sub> mA	V <sub>GS</sub> V	P <sub>D</sub> W
				Min.	Max.	mA				
<b>N-channel</b>										
ZVN2110E	100	320	3	0.8	2.4	1	4	1000	10	0.85
ZVN2106E	60	450	3	0.8	2.4	1	2	1000	10	0.85
ZVN4206E	60	600	3	1.3	3.0	1	1.5	500	5	0.85
ZVN3306E	60	270	3	0.8	2.4	1	5	500	10	0.85
<b>P-channel</b>										
ZVP2110E	-100	-230	-3	-1.5	-3.5	-1	8	-375	-10	0.85
ZVP2106E	-60	-280	-3	-1.5	-3.5	-1	5	-500	-10	0.85
ZVP3306E	-60	-160	-1.6	-1.5	-3.5	-1	14	-200	-10	0.85
<b>Complementary</b>										
ZVC2106E	60	280	3	0.8	3.5	1	5	500	10	0.85

## BIPOLAR QUADS (E = Plastic D.I.L. J = Ceramic D.I.L.)

at 25°C ambient temperature (each transistor)

Type	V <sub>CEO</sub> Volts	Maximum Ratings			h <sub>FE</sub>		Max. V <sub>CE(sat)</sub> at		Min f <sub>T</sub>	
		V <sub>CEO</sub> Volts	I <sub>C</sub> mA	P <sub>D</sub> * mW	Min./Max. at	I <sub>C</sub>	V <sub>CE(sat)</sub> Volts	I <sub>C</sub> mA	MHz at	I <sub>C</sub> mA
FF2221E	60	40	500	400	40/-	150	0.4	150	200	20.0
FF2221J	60	40	600	750	40/-	150	0.4	150	200	20.0
FF2222E	60	40	500	400	100/-	150	0.4	150	200	20.0
FF2222J	60	40	600	750	100/-	150	0.4	150	200	20.0
FF2483E	60	40	100	400	150/-	1	0.35	1	175+	0.5
FF2483J	60	40	100	600	150/-	1	0.35	1	175+	0.5
FF2484E	60	40	100	400	300/-	1	0.35	1	175+	0.5
FF2484J	60	40	100	600	300/-	1	0.35	1	175+	0.5
FF2906E	-60	-40	-600	600	40/-	-150	-0.4	-150	200	-50.0
FF2906J	-60	-40	-600	750	40/-	-150	-0.4	-150	200	-50.0
FF2907E	-60	-40	-600	600	100/-	-150	-0.4	-150	200	-50.0
FF2907J	-60	-40	-600	750	100/-	-150	-0.4	-150	200	-50.0
FF3467J	-40	-40	-1000	900	20/-	-500	-0.5	-500	190+	-50.0
FF3725EA	60	40	500	600	35/200	100	0.3	100	250	50.0
FF3725JA	60	40	1500	750	35/250	100	0.26	100	325+	50.0

\*Power dissipation per transistor +Typical

Pin Configurations overleaf